

	Type	L #	Hits	Search Text	DBs
1	BRS	L1	2	6632750.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
2	BRS	L2	331	438/761.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
3	BRS	L3	346	438/762.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
4	BRS	L4	333	438/791.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
5	BRS	L5	177	(first adj silicon adj nitride) and substrate and CVD and ammonia and (second adj silicon adj nitride)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
6	BRS	L6	26	(first adj silicon adj nitride) and substrate and CVD and ammonia and (second adj silicon adj nitride) and (third adj silicon adj nitride)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
7	BRS	L8	66	substrate and (low adj pattern adj density) same (high adj pattern adj density)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
8	BRS	L9	1543	(silicon adj nitride) and (silicon adj oxide) and (sidewall and spacer\$1) and (gate adj electrode) and contact	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB

	Time Stamp
1	2004/01/16 14:01
2	2004/01/16 14:01
3	2004/01/16 14:01
4	2004/01/16 14:02
5	2004/01/16 14:03
6	2004/01/16 14:03
7	2004/01/16 14:05
8	2004/01/16 14:06